

**IN THE CLAIMS:**

**Please cancel** claims 43 and 44. **Please also amend** claims 1, 2, and 37, as shown in the complete list of claims that is presented below.

1. (currently amended) A heat radiation structure of a semiconductor device, comprising:

a substrate having, on a surface thereof, a first area on which the semiconductor device is mounted, and a second area which surrounds the first area; and

the semiconductor device having a first surface and a second surface opposite to the first surface, the second surface having a periphery, the semiconductor device additionally having a plurality of terminals provided on the first surface,

wherein the semiconductor device is mounted on the substrate in such a manner that the first surface is opposite to the surface of the substrate,

wherein a first heat radiating film is disposed on the second area of the substrate, and a second heat radiating film is disposed on the second surface of the semiconductor device but does not extend beyond the periphery of the second surface, with the second heat radiating film being spaced apart from the first heat radiating film;

wherein the first and second heat radiating films are independent of each other and are disposed at different distances from the substrate; and

wherein the second heat radiating film has a peripheral edge and a rear side that are exposed to air.

2. (currently amended) A heat radiation structure of a semiconductor device, comprising:

a substrate with the semiconductor device mounted on the surface thereof; and

the semiconductor device, which includes a first surface, a second surface opposite to the first surface and having a periphery and a plurality of side surfaces provided between the first surface and the second surface, the semiconductor device being provided with a plurality of terminals on the first surface,

wherein the semiconductor device is mounted on the substrate in such a manner that the first surface is opposite to the surface of the substrate,

wherein a first heat radiating film is disposed on the substrate adjacent the semiconductor device,

wherein a second heat radiating film is disposed on the second surface of the semiconductor device without extending beyond the periphery of the second surface, and exposes the side surfaces of the semiconductor device, the second heat radiating film being independent of the first heat radiating ~~film~~; and film,

wherein the second heat radiating film has a peripheral edge and a rear side that are exposed to ~~[[air.]]~~ air, and

wherein the first and second heat radiating films are disposed at different distances from the substrate.

3. (original) A heat radiation structure according to claim 1, wherein the substrate is provided with external electrodes connected to an external board.

4. (original) A heat radiation structure according to claim 1, wherein the substrate is provided with external electrodes connected to an external board, and the semiconductor device is mounted on the substrate in plural form.

5. (original) A heat radiation structure according to claim 1, wherein the substrate includes external electrodes connected to an external board, and the external electrodes are formed on the back of the substrate.

6. (original) A heat radiation structure according to claim 1, wherein wirings are formed on the surface of the substrate, and the terminals of the semiconductor device and the wirings of the substrate are electrically connected to one another.

7. (original) A heat radiation structure according to claim 1, wherein the semiconductor device includes a semiconductor element formed with an electronic circuit and a resin layer formed on the semiconductor element, and the terminals are formed on the resin layer.

8. (original) A heat radiation structure according to claim 1, wherein the surfaces of the first and second heat radiating films are exposed.

9. (original) A heat radiation structure according to claim 1, wherein wirings are formed on the surface of the substrate, and the first heat radiating film is formed so as to cover the wirings.

10. (original) A heat radiation structure according to claim 1, wherein openings are defined in the first heat radiating film, and parts of the surface of the substrate are exposed through the openings.

11. (original) A heat radiation structure according to claim 1, wherein openings are defined in the second heat radiating film, and parts of the second surface of the semiconductor device are exposed through the openings.

12. (original) A heat radiation structure according to claim 1, wherein a seal is applied onto the second surface of the semiconductor device, openings are defined in the second heat radiating film, and the openings are provided such that the seal is exposed.

13. (original) A heat radiation structure according to claim 1, wherein the thickness of each of the first and second heat radiating films ranges from 30 $\mu$ m to 200 $\mu$ m.

14. (original) A heat radiation structure according to claim 1, wherein the first and second heat radiating films respectively comprise a common material.

15. (original) A heat radiation structure according to claim 1, wherein the first heat radiating film and the second heat radiating film are different in thermal expansion coefficient.

16. (original) A heat radiation structure according to claim 1, wherein a film having an insulating property is used for the first and second heat radiating films.

17. (original) A heat radiation structure according to claim 1, wherein a thermal emission film having thermal radiation is used for the first and second heat radiating films.

18. (original) A heat radiation structure according to claim 1, wherein the material for the first and second heat radiating films is ceramics.

19. (original) A heat radiation structure according to claim 1, wherein the material for the first and second heat radiating films is silica alumina ceramics.

Claims 20-33 (cancelled).

34. (previously presented) A heat radiating structure according to claim 2, wherein the heat radiating film is made of ceramic material.

Claims 35-36 (cancelled).

37. (currently amended) A heat radiation structure in combination with a semiconductor device with a wafer level chip size package, the semiconductor device having a first surface with terminals and having a second surface with a periphery, the second surface of the semiconductor device being oriented opposite the first surface, said heat radiation structure comprising:

a substrate having, on a surface thereof, a first area and a second area adjacent the first area, the semiconductor device being mounted on the first area of the substrate with the first

surface of the semiconductor device facing the substrate, the semiconductor device covering the first area;

a first heat radiating film on the substrate in the second area; and

a second heat radiating film disposed on the second surface of the semiconductor device without extending beyond the periphery of the second surface and without overlapping the first heat radiating film, the second heat radiating film being independent of the first heat radiating film and having a peripheral edge and a rear side that are exposed to [[air.]] air,

wherein the first and second heat radiating films are disposed at different distances from the substrate.

38. (previously presented) A combination according to claim 37, wherein the first heat radiating film is made of ceramic material.

39. (previously presented) A combination according to claim 37, wherein the second heat radiating film is made of ceramic material.

40. (previously presented) A combination according to claim 37, wherein the first and second heat radiating films are made of ceramic material.

41. (previously presented) A heat radiating structure according to claim 1, wherein the first heat radiating film is thinner than the semiconductor device, and has a rear side that is exposed to air.

42. (previously presented) A heat radiating structure according to claim 37, wherein the first heat radiating film is thinner than the semiconductor device, and has a rear side that is exposed to air.

Claims 43-44 (cancelled).